

formed at an upper part of said glass substrate, a channel region, a source region, a drain region, a first insulating layer and a second insulating layer, wherein:

said channel region, said source region and said drain region comprise polycrystalline silicon,

C said glass substrate is such that its compaction is 30 ppm or higher, when said glass substrate is heated at 600° C for 1 hour and thereafter cooled at a rate of 1° C/minute,

said first insulating layer covers said channel region and has a layer thickness whose lower limit is 4nm, and

said second insulating layer is formed on a surface of said first insulating layer.

Ex note
9. (Twice Amended) A thin-film transistor comprising:

a glass substrate; and

formed at an upper part of said glass substrate, a channel region, a source region, a drain region and an insulating layer, wherein:

said channel region, said source region and said drain region comprise polycrystalline silicon,

said glass substrate is such that its compaction is 30 ppm or higher, when said glass substrate is heated at 600° C for 1 hour and thereafter cooled at a rate of 1° C/minute, and

said insulating layer covers said channel region and has a layer thickness defined by the range 4nm to 20nm.